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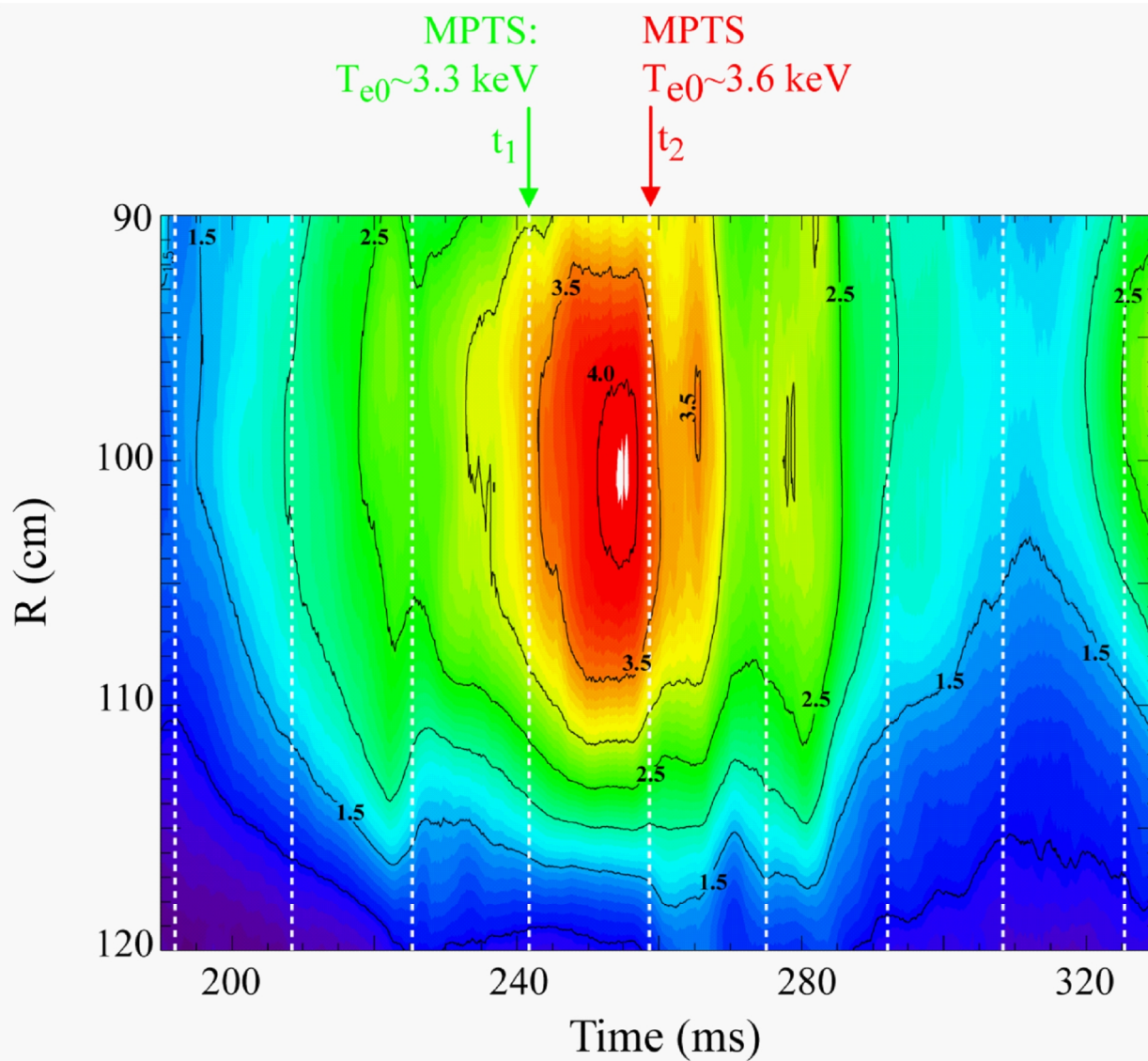
Prototype Multi-Energy Soft X-ray Diagnostic for EAST

presented by

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Johns Hopkins University
Baltimore, MD USA

ME-SXR fast T_e technique used to reconstruct RF heated T_e profile between MPTS measurements

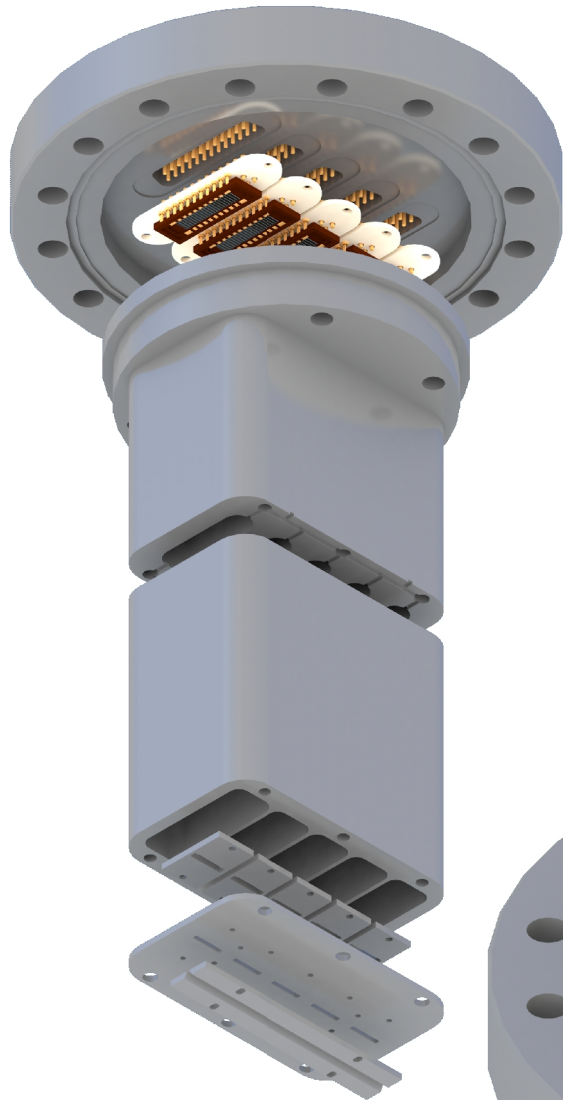


L. Delgado-Aparicio, et al., JAP, **102**, 073304 (2007).

L. Delgado-Aparicio, et al., PPCF, **49**, 1245 (2007).

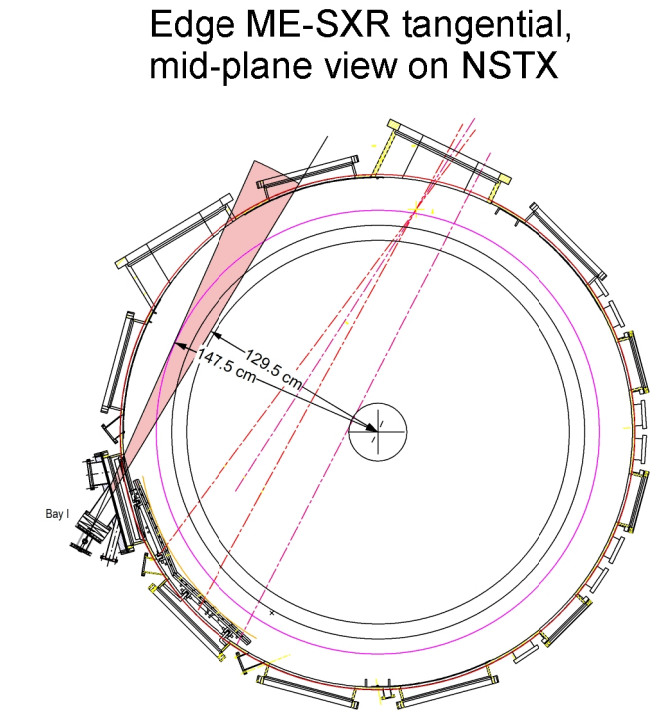
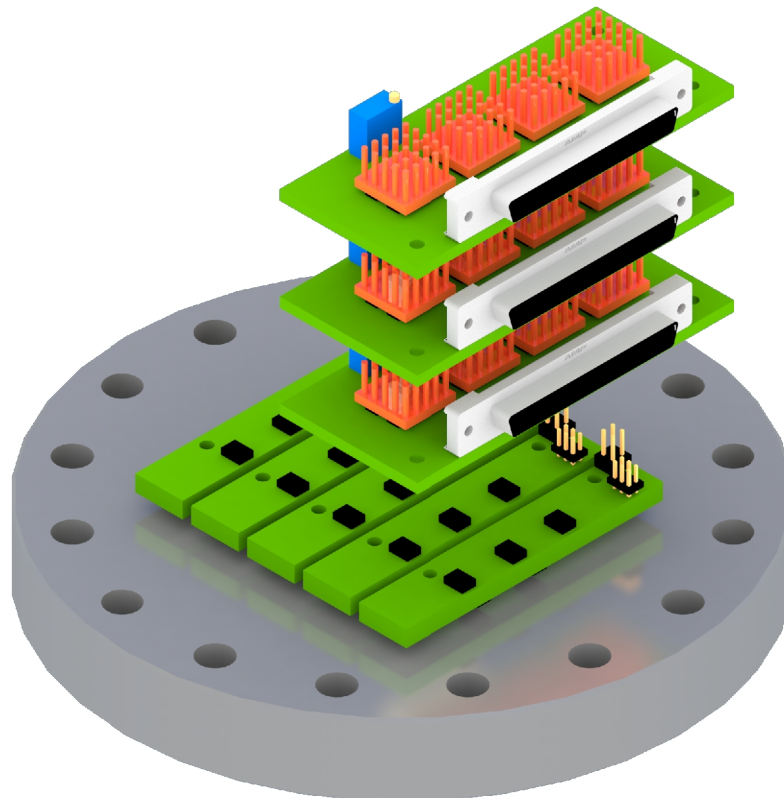
- Reconstructed T_e shows peak >4 keV, $\sim 15\%$ higher than MPTS measurement
- MPTS profiles used to cross-check ME-SXR reconstruction, provide normalization

Original diode-based ME-SXR system operated on NSTX during 2010 run



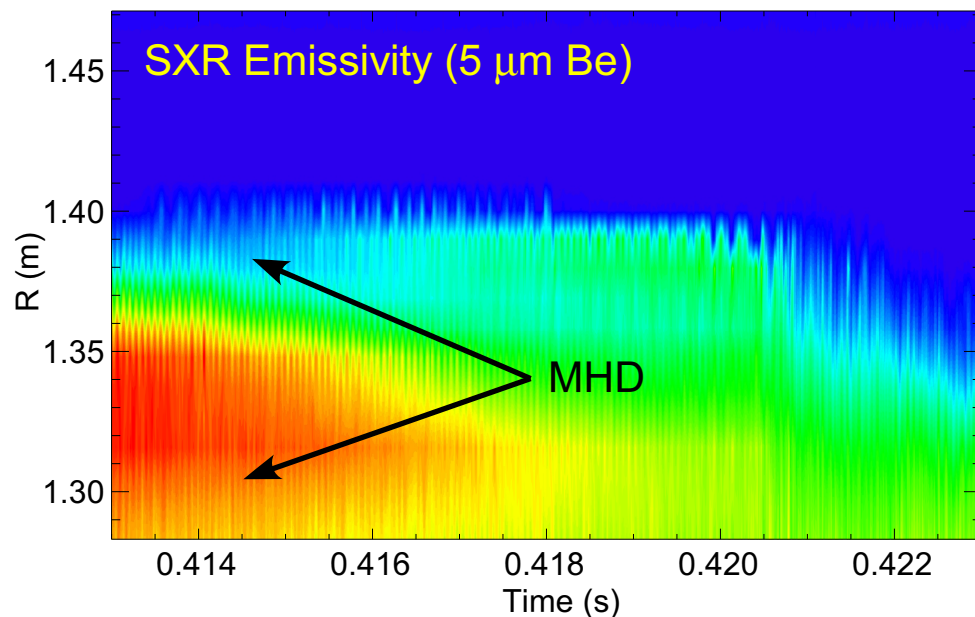
vacuum hardware mounted on 6" Conflat

attached to port-mounted gate valve

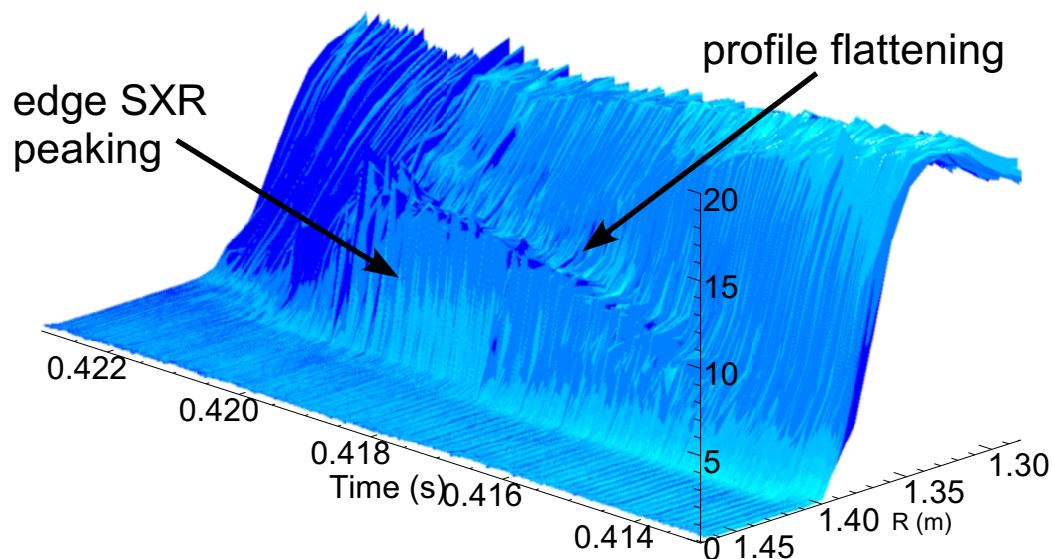


amplifiers mounted on back (atmosphere-side) of Conflat flange

Abel inversion of tangential ME-SXR data shows detailed edge dynamics before profile crash

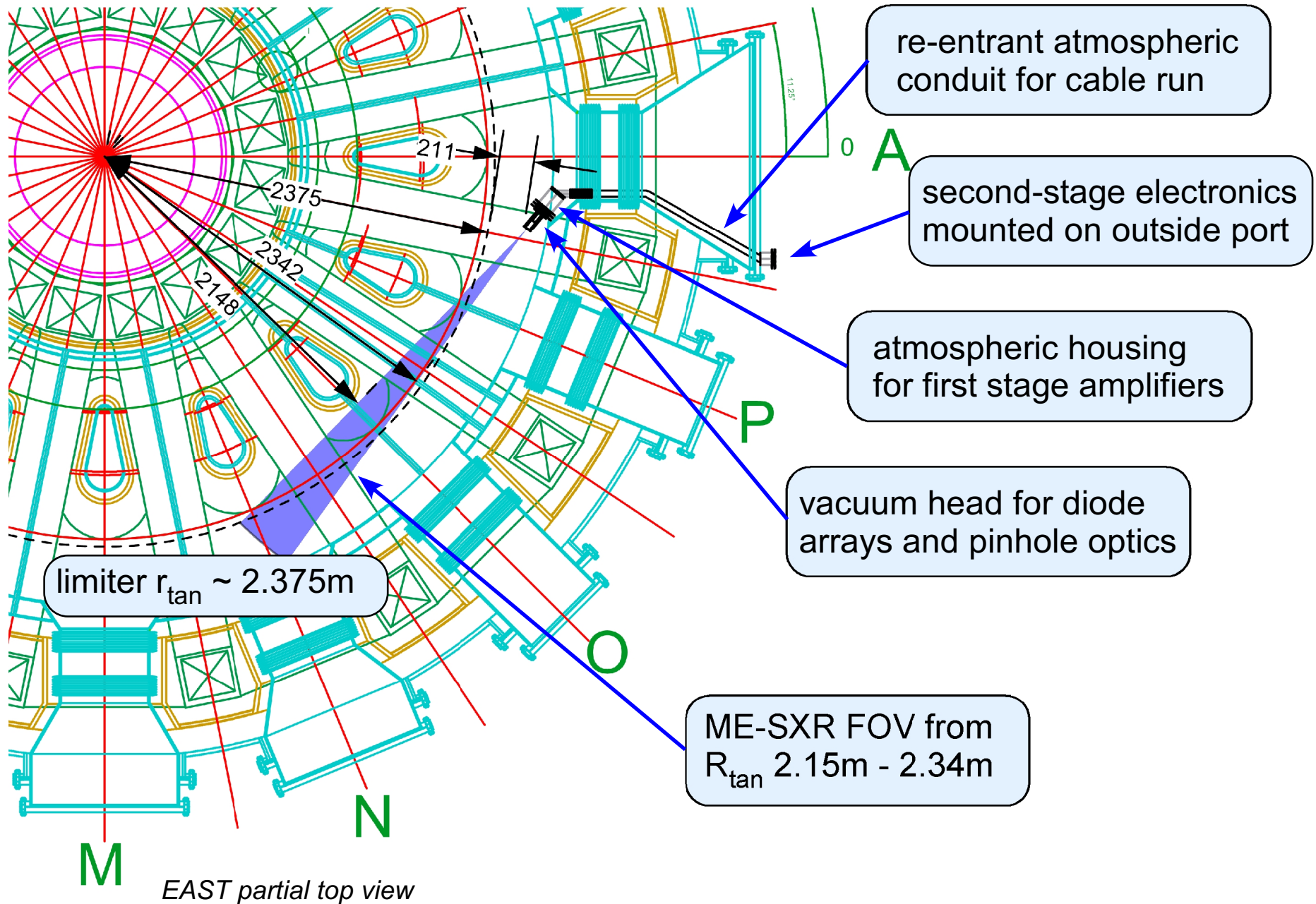


- 16 kHz internal MHD mode coupled to edge
- edge MHD slows prior to profile crash

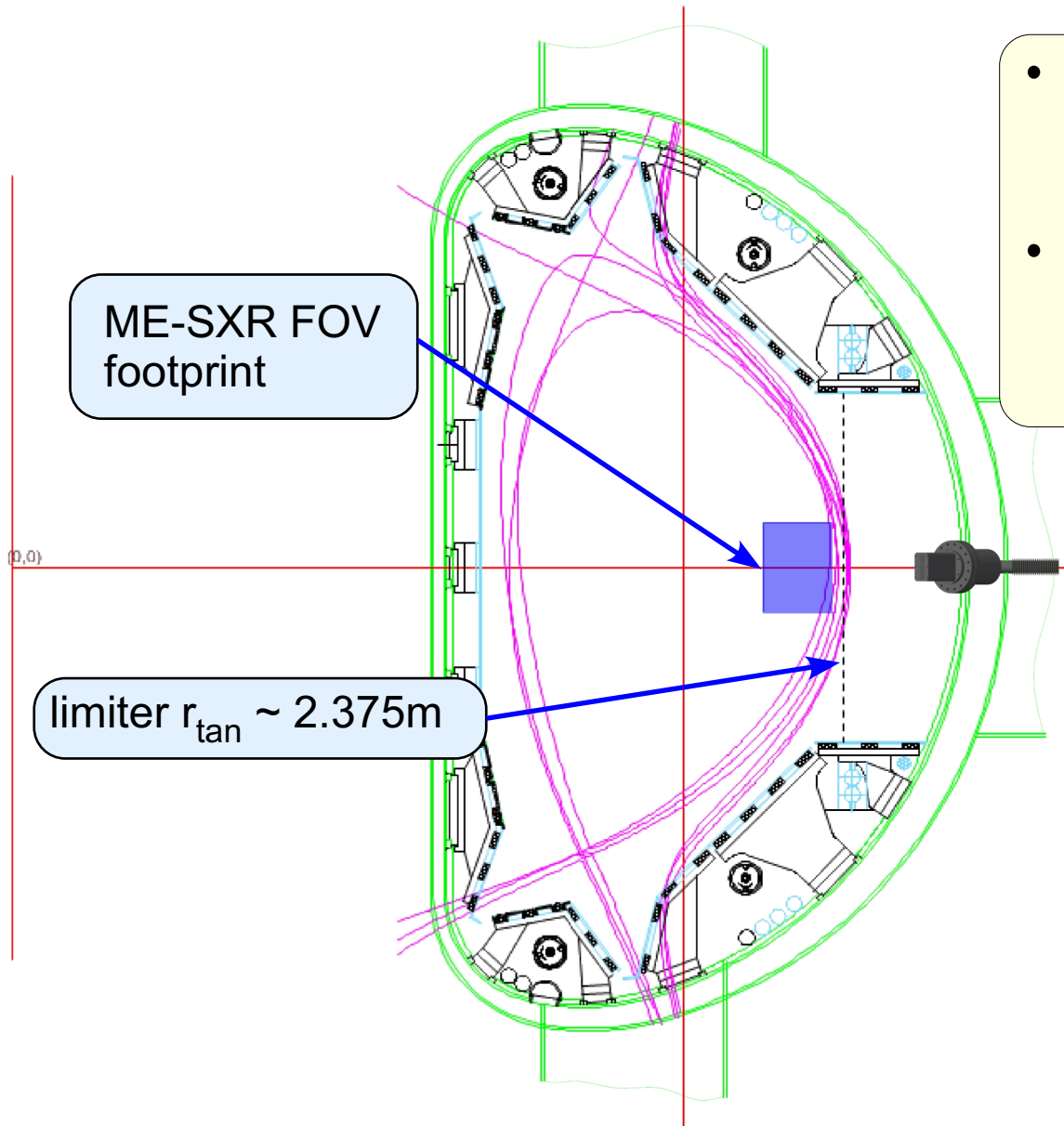


- SXR profile begins to flatten
- strong steepening of edge emission profile prior to crash (possible C accumulation?)

Atmospheric re-entrant 'in-vessel' design necessary to accommodate EAST port geometry

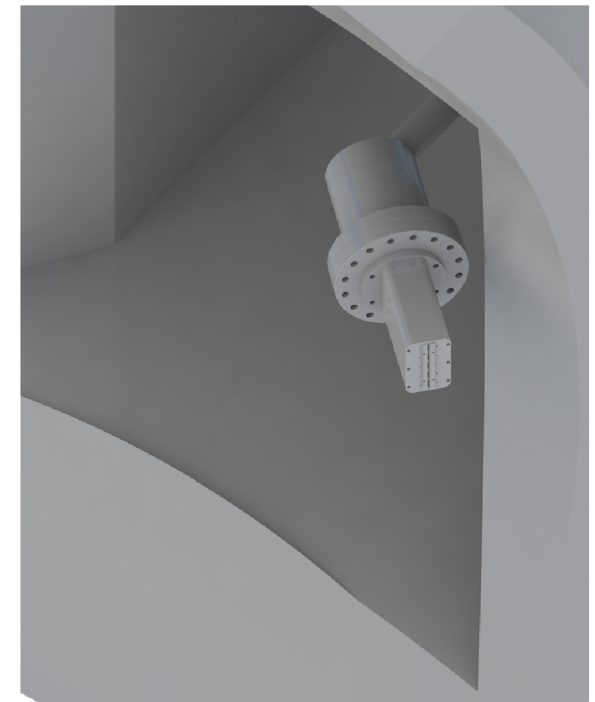


ME-SXR assembly to be mounted at mid-plane on port side wall



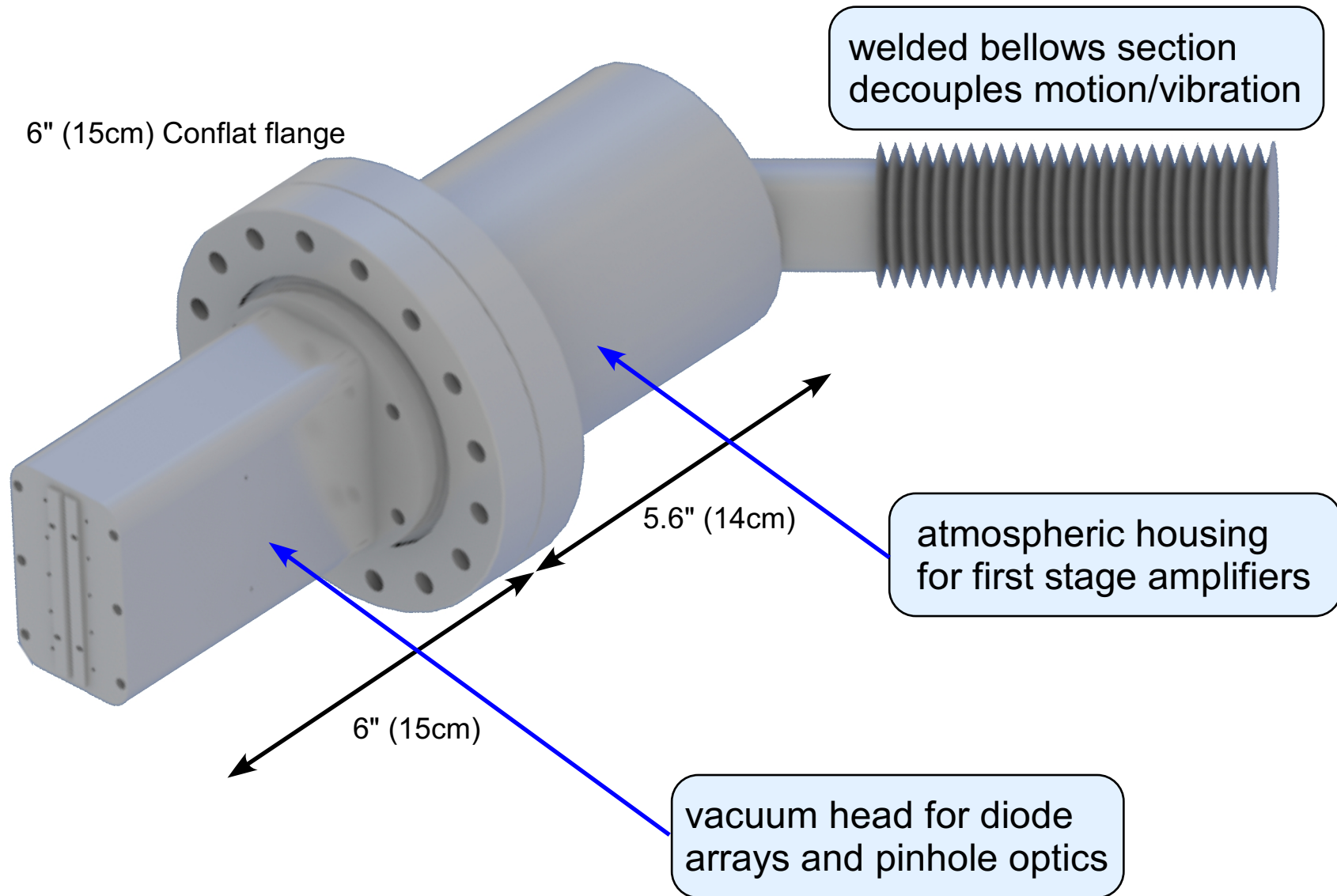
EAST side view

- ME-SXR provides coverage from edge to mid-radius
- FOV footprint in plasma can be adjusted by changing mounting position/angle

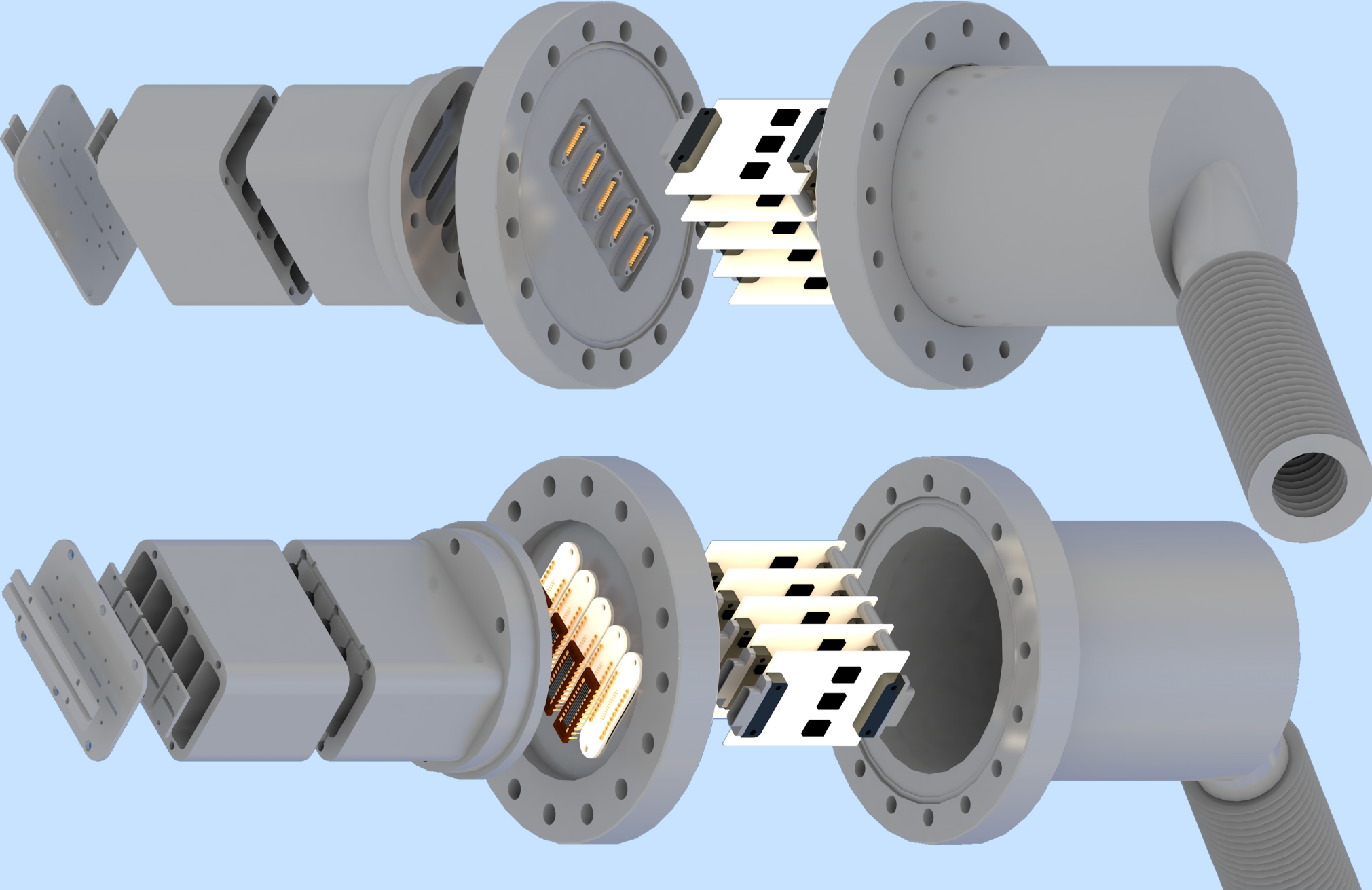


3D view of ME-SXR

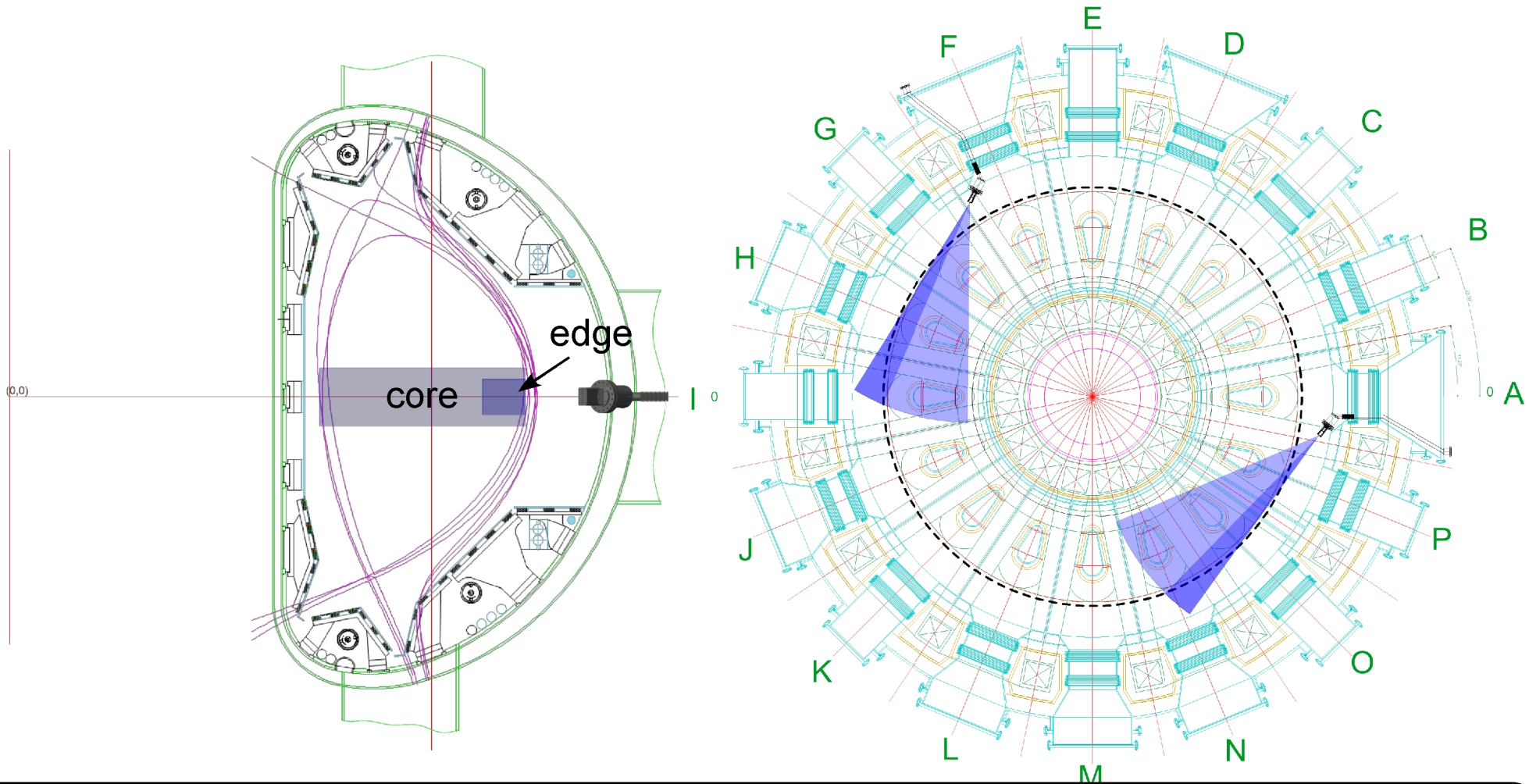
In-vessel housing provides compact system for ease of mounting



Expanded view of ME-SXR assembly



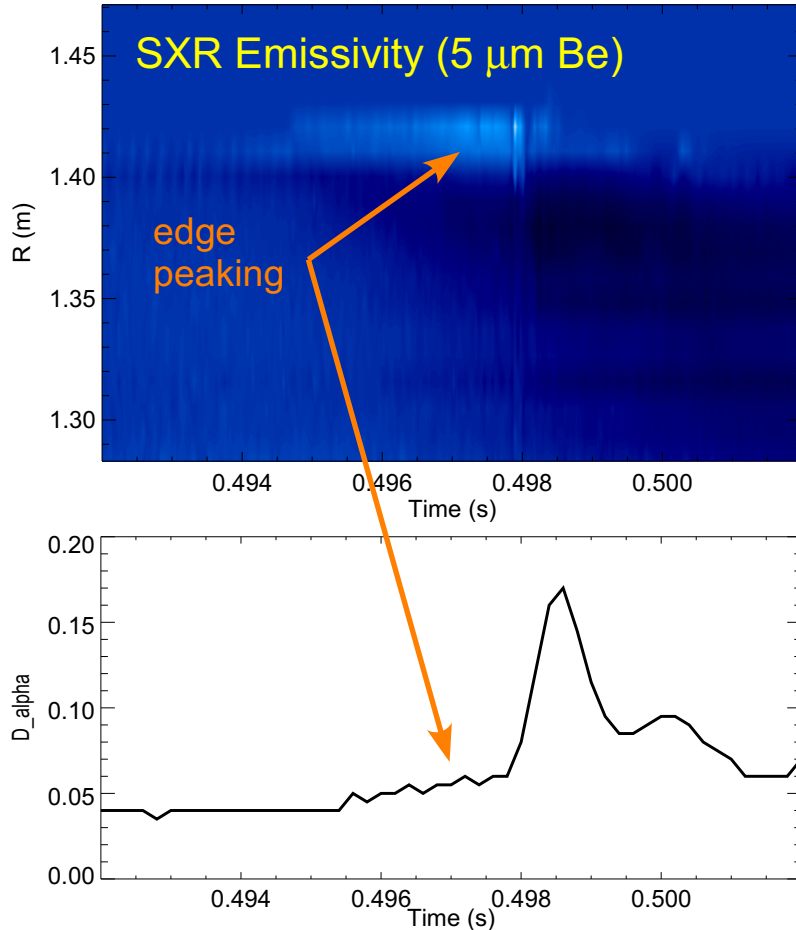
Toroidally-displaced core/edge ME-SXR systems currently proposed for EAST under DOE international solicitation



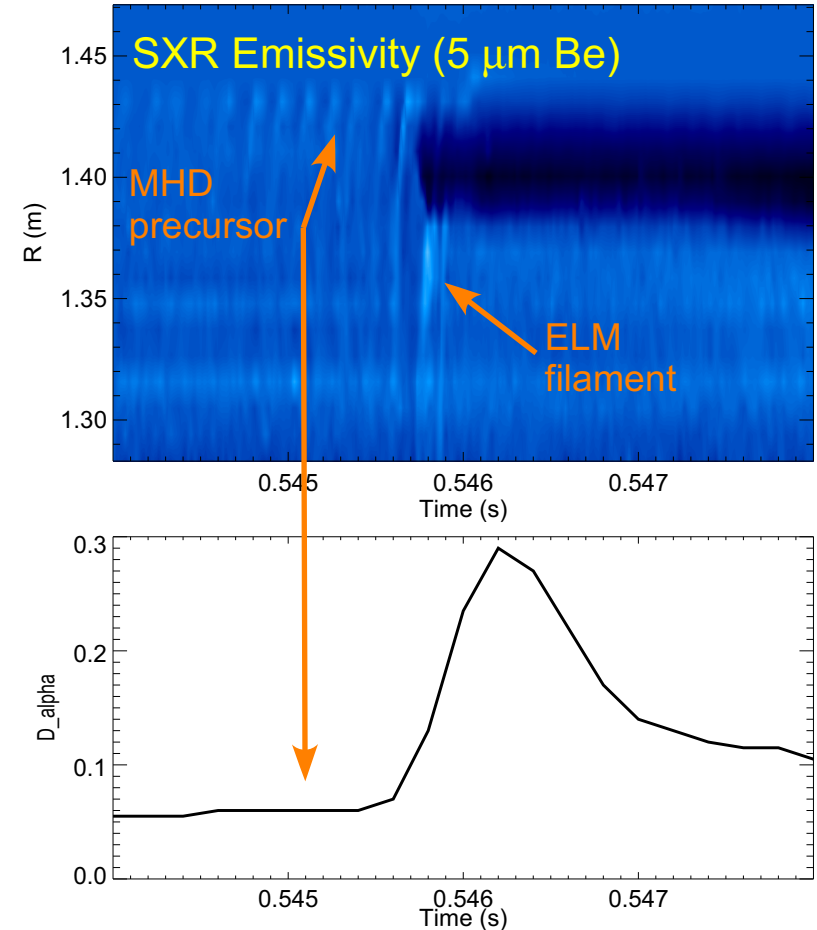
- ME-SXR proposed in “International collaboration to advance the three dimensional science of stability and control for long-pulse, high-performance tokamaks” Gates/Sabbagh
- System designed to study lithium effects on ELM and MHD/NTM behavior, disruption precursors and thermal quench, and positioned to study effects of planned 3D coils on plasma

Thank You

Time/spatial resolution of ME-SXR allows investigation of different ELM cycle dynamics



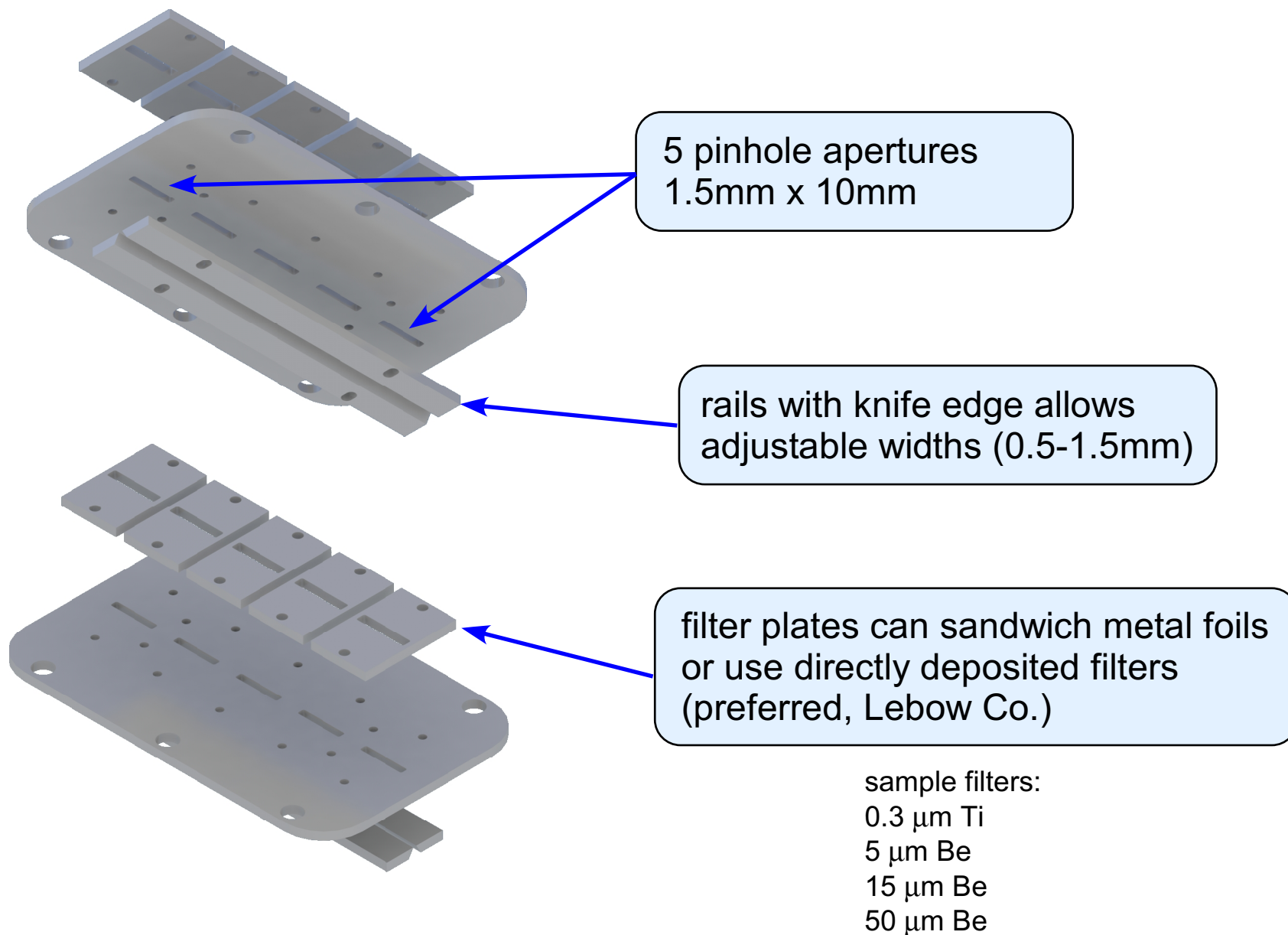
- MHD precursor leads to profile flattening, edge peaking of SXR
- ELM causes broad profile crash



- MHD precursor leads to large ELM filament
- ELM crash limited to edge

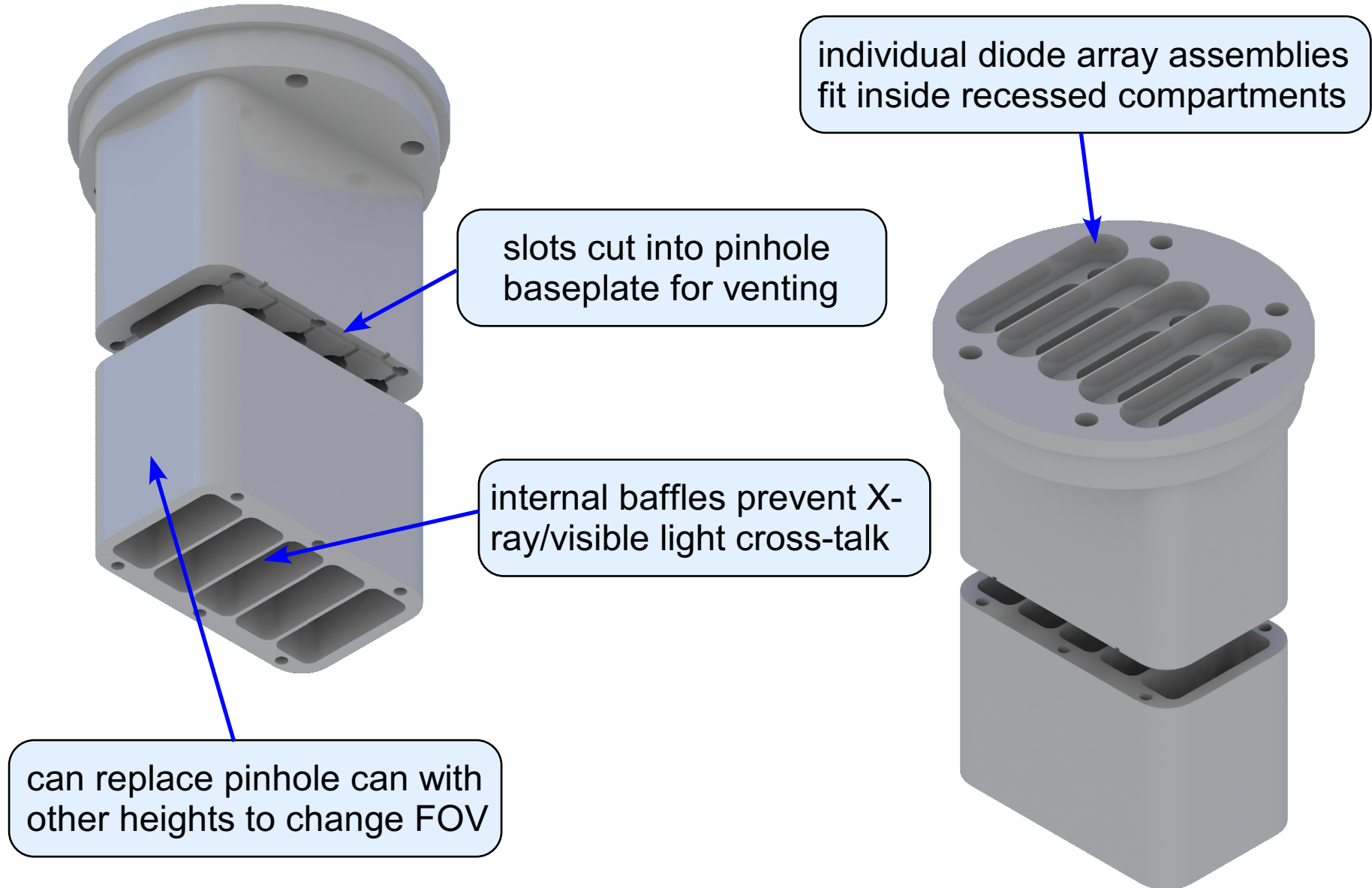
Pinhole assembly provides separate apertures for each diode array

material: 303/304 Stainless Steel

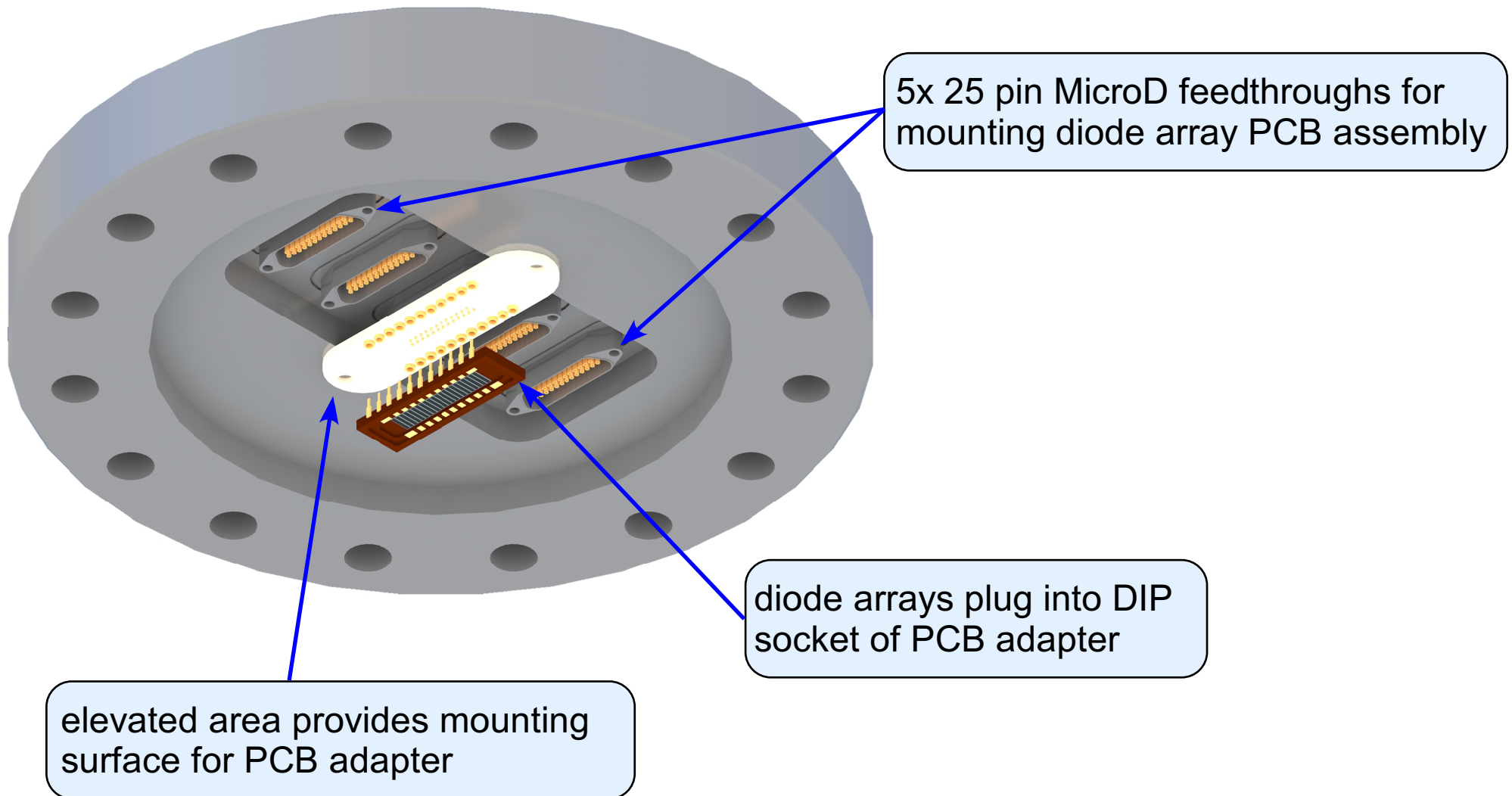


Pinhole can assembly uses separate compartments to eliminate cross-talk between arrays

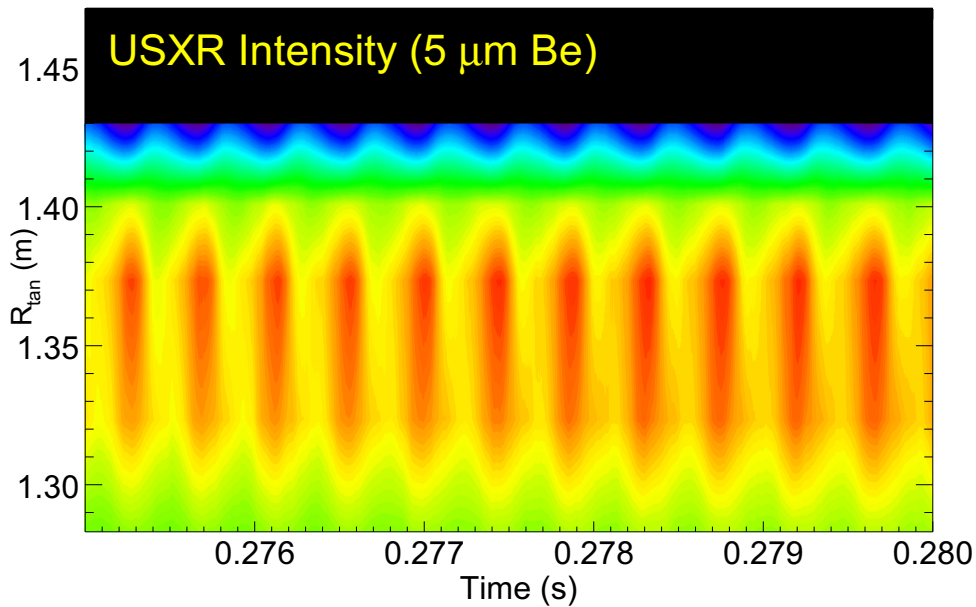
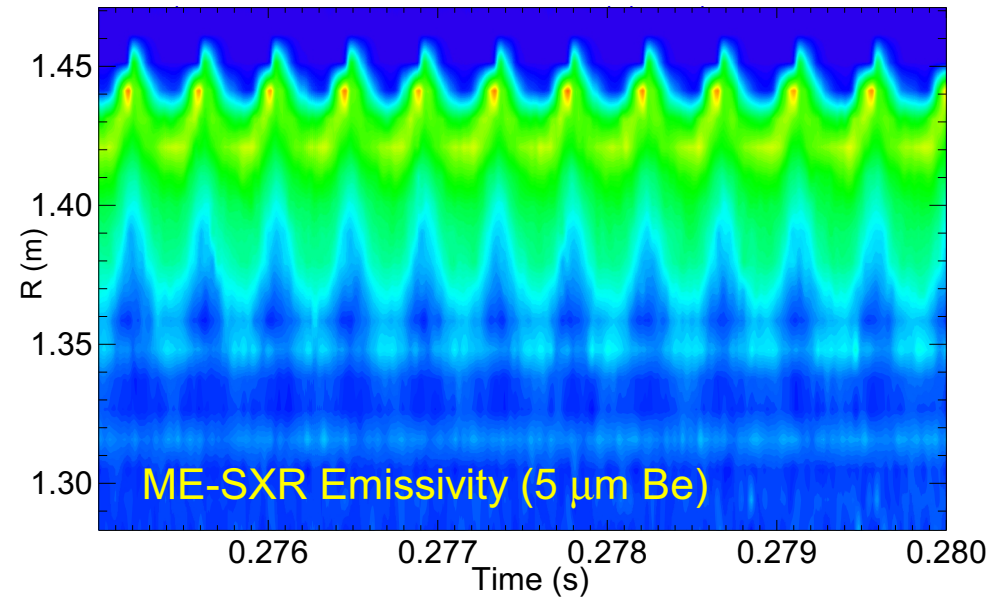
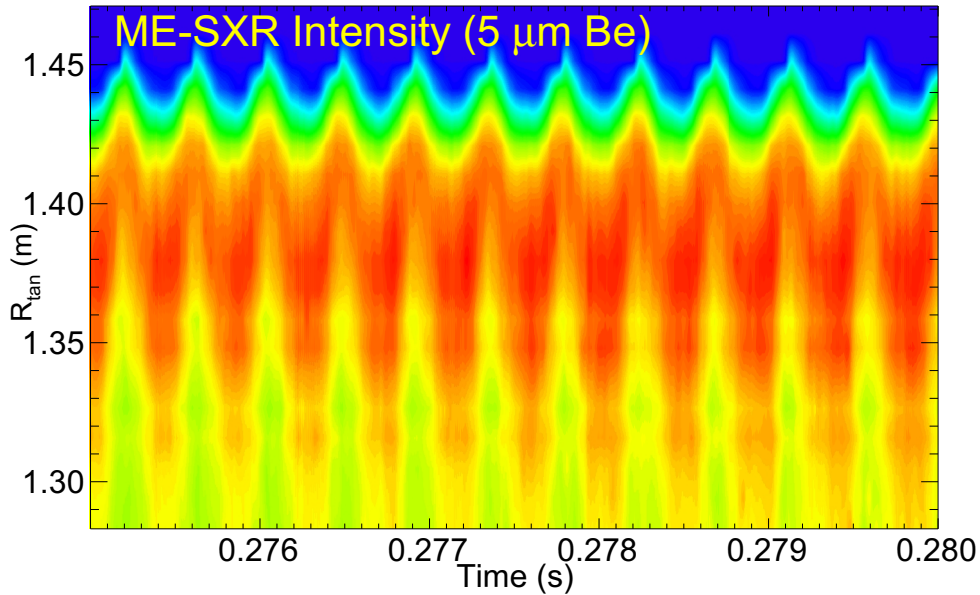
material: 303/304 Stainless Steel



Conflat flange uses 25 pin MicroD vacuum feedthroughs



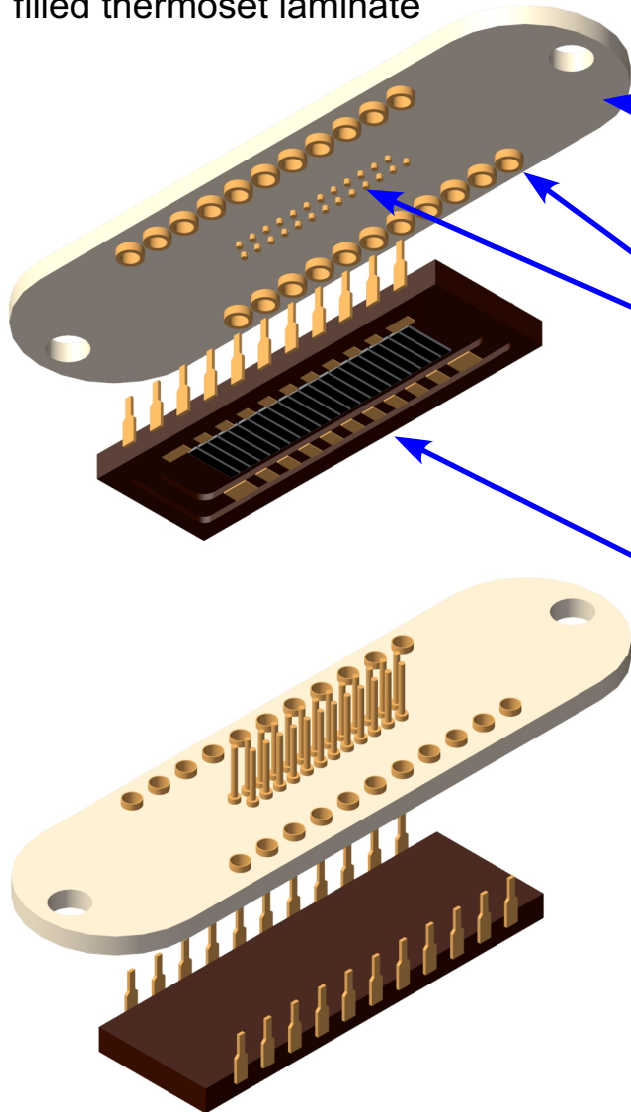
High spatial resolution measures strong localization of emission during edge MHD activity



- Inversion shows highly localized MHD, $\Delta r \sim 1 \text{cm}$ SXR emission near edge (possible carbon accumulation?)
- High spatial resolution and Abel inversion provide advantages over poloidal USXR system

PCB diode adapter uses low-outgassing laminate material

RO4003 glass woven/ceramic filled thermoset laminate



custom PCB adapter uses Rogers 4003 laminate (RO3003 used in NSTX, RO4003 used in LTX)

Mill-Max pin/sockets used for DIP22 to MicroD25 adapter layout

AXUV20 diode array from OptoDiode (formerly IRD Inc.) 20x 0.75mm x 4mm elements

system bakeable up to 125-150 °C

Materials outgassing comparison (NASA)

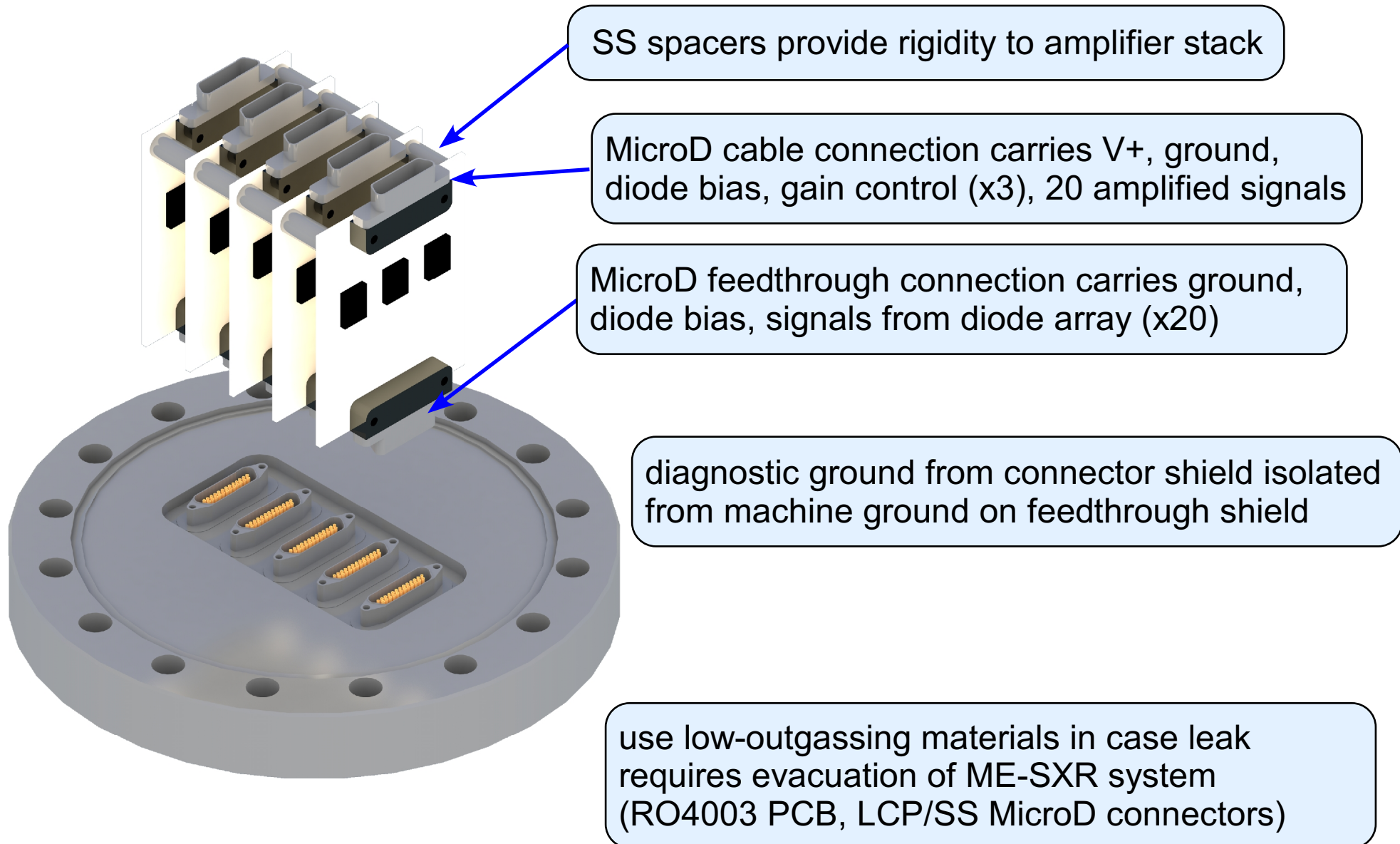
Material	%TML	%CVCM	%WVR
RO4003	0.06	0.00	0.02
Vespel	1.0	0.00	0.40
PEEK	0.14	0.00	0.05
FR4	0.3	0.01	0.1
LCP	0.06	0.01	0.01

TML = total mass loss

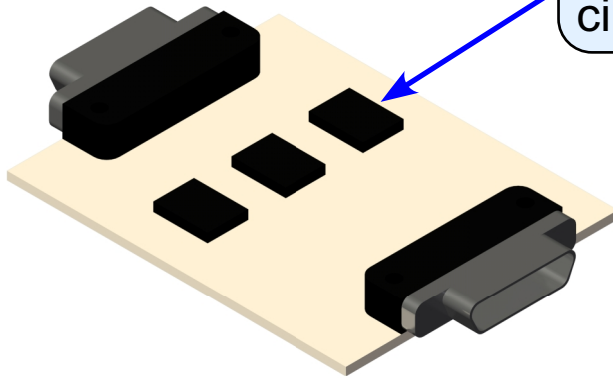
CVCM = collected volatile condensable materials

WVR = water vapor regained

Switch to MicroD connectors allows compact stacking of first stage amplifier boards

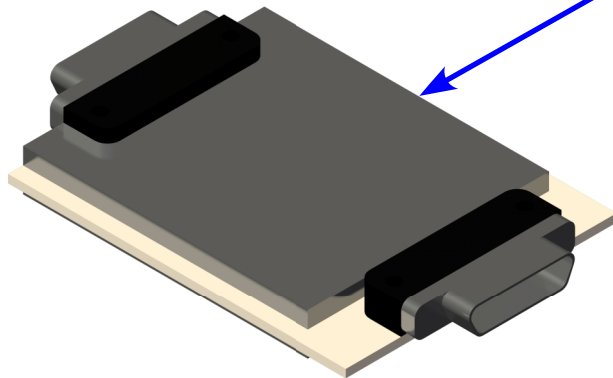


Initial amplifier system similar to NSTX/LTX circuit design



larger board layout provides room for enhanced power circuitry and MicroD connectors for robust mating

multi-channel variable gain transimpedance amplifiers provide signal flexibility

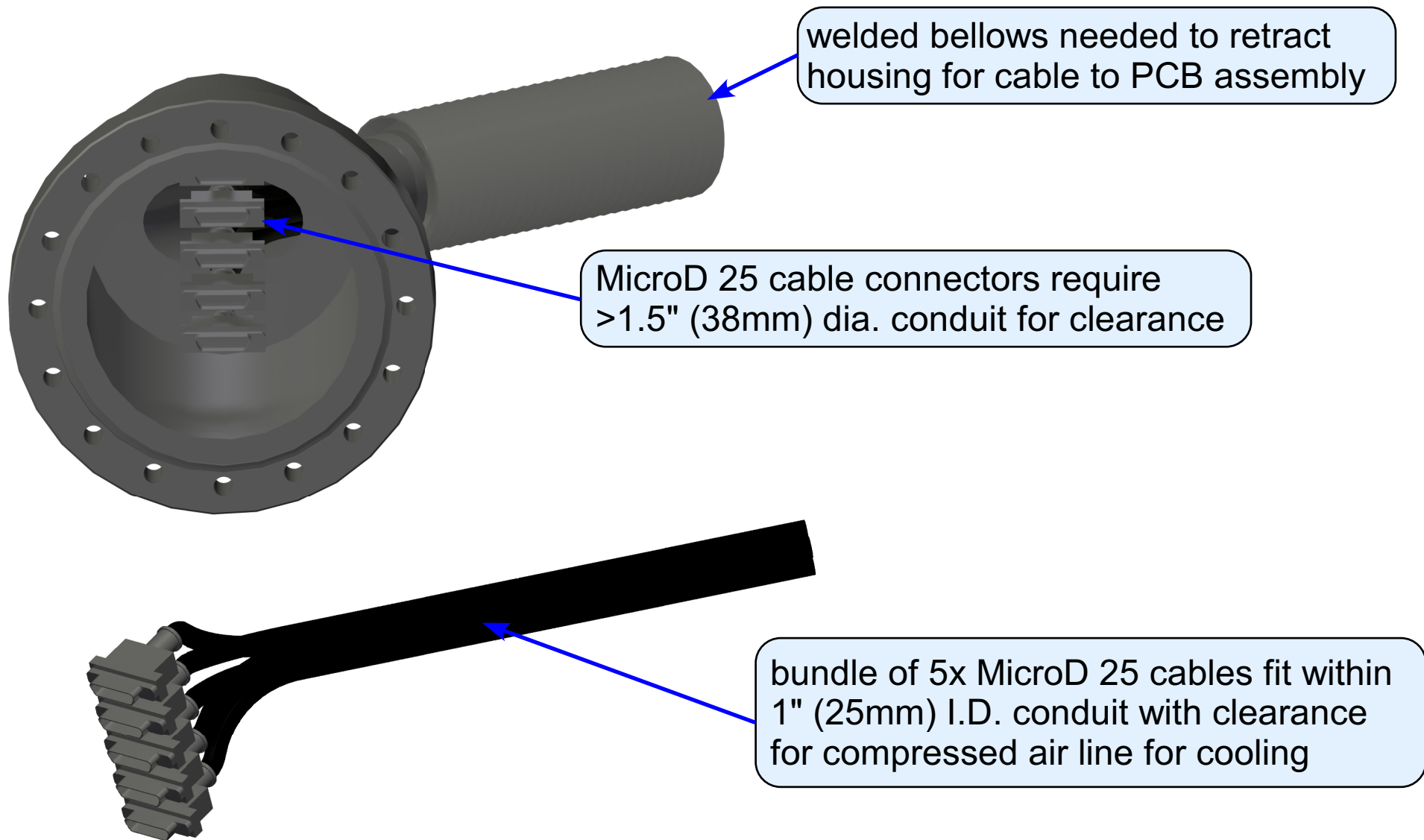


option for EMI shielding of first stage amplifier circuits under consideration

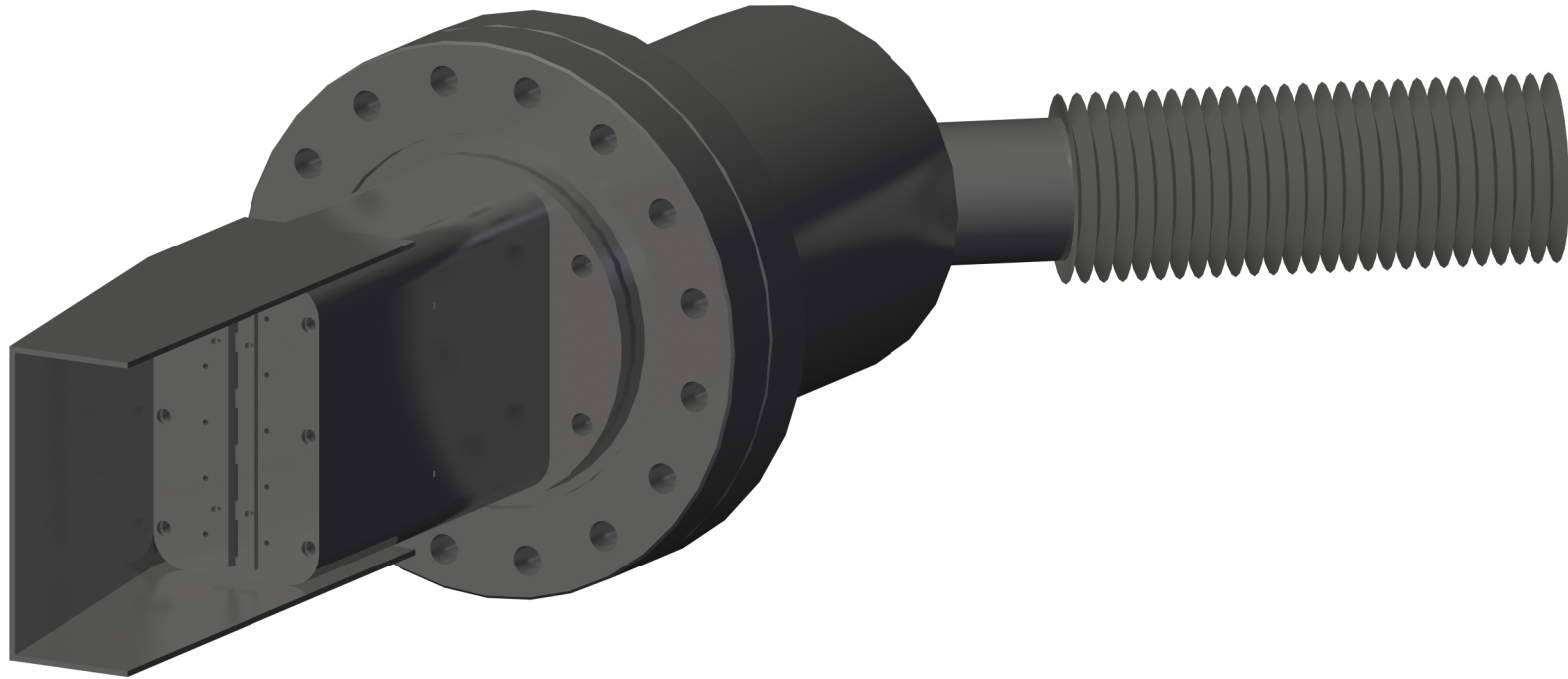
Two other modifications under development

- on-board ADC: convert to serial output
5x MicroD 25 cables \Rightarrow 1x MicroD 31
- use UHV ICs and connectors for first-stage, in-vacuum amplification (requires cooling)

5x MicroD 25 cabling carry amplified signals to second stage electronics



Line-of-sight shielding protects filters from lithium deposition and sputtering



complete shuttering of view would be preferable though may be difficult given port access